NSN 5961-01-326-2359

Transistor - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5961-01-326-2359

Inclosure Material:

Metal

Overall Length:

1.260 inches

Overall Height:

Between 0.250 inches and 0.340 inches

Overall Width:

0.700 inches

Mounting Facility Quantity:

2

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-213aa

Electrode Internally-electrically Connected To Case:

Drain

Mounting Method:

Unthreaded hole

Features Provided:

Burn in and electrostatic sensitive and quality assurance level tx

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

500.0 drain to source voltage and 500.0 drain to gate voltage

Current Rating Per Characteristic:

6.00 amperes drain current

Power Rating Per Characteristic:

70.0 watts total power dissipation

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 pin and 1 case

Specification Data:

81349-mil-s-19500/569 government specification

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0